

TSA1765



High Voltage PNP Epitaxial Planar Transistor

SOT-223

Pin Definition:

- 1. Base
 - 2. Collector 3. Emitter

PRODUCT SUMMARY

BV _{CBO}	-560V
BV _{CEO}	-560V
Ic	-150mA
V _{CE(SAT)}	-0.5V @ I _C =-50mA,I _B =-10mA

Ordering Information

Part No.	Package	Packing		
TSA1765CW RP	SOT-223	2.5Kpcs / 13" Reel		

Features

- Low Saturation Voltages
- High Breakdown Voltage

Structure

- Epitaxial Planar Type
- PNP Silicon Transistor

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	-560	V
Collector-Emitter Voltage	V_{CEO}	-560	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current	I _C	-150	
Collector Current(Pulse)	I _{CP}	-500	mA
Base Current	I _B	-50	
Total Power Dissipation @ T _C =25°C	P _{tot}	2	W
Operating Junction Temperature	TJ	+150	°C
Operating Junction and Storage Temperature Range	T _{STG}	- 55 to +150	°C

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	$I_{C} = -1 \text{mA}, I_{E} = 0$	BV _{CBO}	-560			V
Collector-Emitter Breakdown Voltage	$I_{C} = -1 \text{mA}, I_{B} = 0$	BV _{CEO}	-560			V
Emitter-Base Breakdown Voltage	$I_E = -10uA, I_C = 0$	BV _{EBO}	-7			V
Collector Cutoff Current	$V_{CB} = -560V, I_{E} = 0$	I _{CBO}			-100	nA
Emitter Cutoff Current	$V_{EB} = -7V, I_{C} = 0$	I _{EBO}			-100	nA
Collector-Emitter Saturation Voltage	$I_{C} = -20 \text{mA}, I_{B} = -2 \text{mA}$	V _{CE(SAT)} 1			-0.2	V
	$I_{\rm C} = -50 \text{mA}, I_{\rm B} = -10 \text{mA}$	V _{CE(SAT)} 2			-0.5	
Base-Emitter Saturation Voltage	$I_{\rm C} = -50 \text{mA}, I_{\rm B} = -10 \text{mA}$	V _{BE(SAT)} 1			-1.0	V
Base-Emitter on Voltage	$V_{CE} = -10V, I_{C} = -50mA$	$V_{BE(ON)}$			-1.0	V
DC Current Transfer Ratio	$V_{CE} = -10V, I_{C} = -1mA$	h _{FE} 1	150			
	$V_{CE} = -10V, I_{C} = -50mA$	h _{FE} 2	80		300	
	$V_{CE} = -10V, I_{C} = -100mA$	h _{FE} 3		15		
Transition Frequency	$V_{CE} = -20V, I_{E} = -10mA$	f _T	50			MHz
Output Capacitance	V _{CB} = -20V, f=1MHz	Cob			8	pF

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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

Figure 1. Static Characteristics

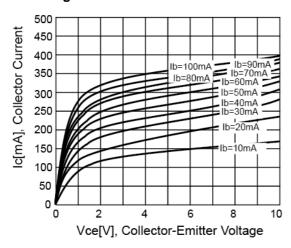


Figure 3. VCE(SAT) v.s. VBE(SAT

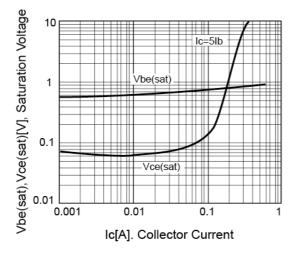


Figure 5. Safety Operation Area

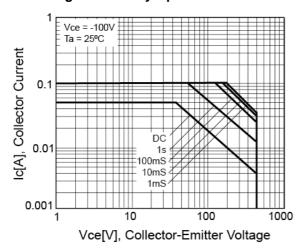


Figure 2. DC Current Gain

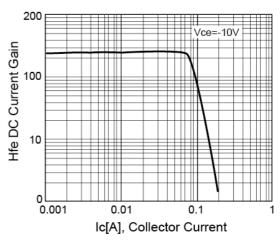
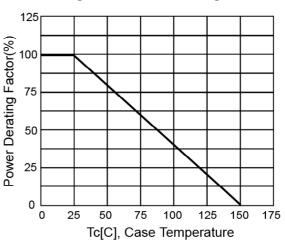


Figure 4. Power Derating



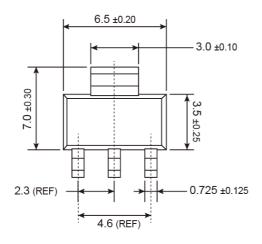
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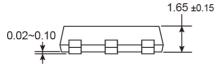


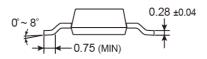


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SOT-223 Mechanical Drawing

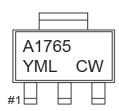






Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code (A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code

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